

Silicon NPN Power Transistors

BU526 BU526A

DESCRIPTION

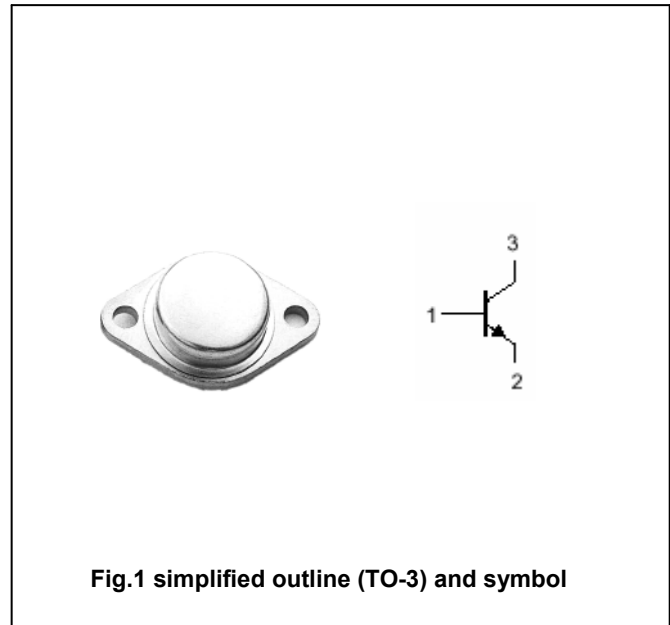
- With TO-3 package
- Short switching times.
- High dielectric strength.

APPLICATIONS

- For use in power supply units of TV receives.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	BU526	400	V
		BU526A	460	
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		10	A
P_T	Total power dissipation	$T_C = 25 \square$	86	W
T_j	Junction temperature		175	\square
T_{stg}	Storage temperature		-65~175	\square

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal resistance junction to case	1.04	\square/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA; I _B =0;	400			V
			460			
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0;	7			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =5A; I _B =1 A			1.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =8A; I _B =3 A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =1 A			1.6	V
I _{CBO}	Collector cut-off current	V _{CB} =900V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	15		45	

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PACKAGE OUTLINE

